

2N6788

File Number 1593

Power MOS Field-Effect Transistors

N-Channel Enhancement-Mode Power Field-Effect Transistors

6.0A, 100V

$r_{DS(on)} = 0.30 \Omega$

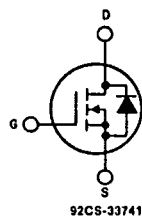
Features:

- SOA is power-dissipation limited
- Nanosecond switching speeds
- Linear transfer characteristics
- High input impedance
- Majority carrier device

The 2N6788 is an n-channel enhancement-mode silicon-gate power field-effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

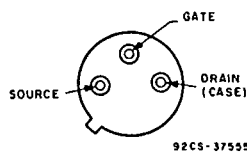
The 2N6788 is supplied in the JEDEC TO-205AF (LOW PROFILE TO-39) metal package.

N-CHANNEL ENHANCEMENT MODE



TERMINAL DIAGRAM

TERMINAL DESIGNATION



JEDEC TO-205AF

Absolute Maximum Ratings

Parameter	2N6788	Units
V_{DS} Drain - Source Voltage (1)	100*	V
V_{DGR} Drain - Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$) (1)	100*	V
$I_D @ T_C = 25^\circ\text{C}$ Continuous Drain Current	6.0*	A
$I_D @ T_C = 100^\circ\text{C}$ Continuous Drain Current	3.5*	A
I_{DM} Pulsed Drain Current (3)	24*	A
V_{GS} Gate - Source Voltage	$\pm 20^*$	V
I_S Continuous Source Current (Body Diode)	6.0*	A
I_{SM} Pulse Source Current (Body Diode) (3)	24*	A
$P_D @ T_C = 25^\circ\text{C}$ Max. Power Dissipation	20* (See Fig. 14)	W
Linear Derating Factor	0.18* (See Fig. 14)	W/ $^\circ\text{C}$
I_{LM} Inductive Current, Clamped	$L = 100 \mu\text{H}$ 24	A
T_J Operating Junction and Storage Temperature Range	-55° to 150°	$^\circ\text{C}$
T_{LW} Lead Temperature	300° (0.063 in. (1.6mm) from case for 10s)	$^\circ\text{C}$

Electrical Characteristics @ $T_C = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS} Drain - Source Breakdown Voltage	100*	—	—	V	$V_{GS} = 0V, I_D = 0.25\text{ mA}$
$V_{GS(th)}$ Gate Threshold Voltage	2.0*	—	4.0*	V	$V_{DS} = V_{GS}, I_D = 1.0\text{ mA}$
I_{GSS} Gate - Source Leakage Forward	—	—	100*	nA	$V_{GS} = 20V, V_{DS} = 0V$
I_{GSS} Gate - Source Leakage Reverse	—	—	100*	nA	$V_{GS} = -20V, V_{DS} = 0V$
I_{DSS} Zero Gate Voltage Drain Current	—	—	250*	μA	$V_{DS} = 100V, V_{GS} = 0V$
$V_{DS(on)}$ On-State Voltage (2)	—	—	1000*	μA	$V_{DS} = 80V, V_{GS} = 0V, T_C = 125^\circ\text{C}$
$R_{DS(on)}$ Static Drain-Source On-State Resistance (2)	—	—	2.10*	V	$V_{GS} = 10V, I_D = 6.0A$
V_{SD} Diode Forward Voltage (2)	—	0.25	0.30*	D	$V_{GS} = 10V, I_D = 3.5A, T_C = 25^\circ\text{C}$
g_{fs} Forward Transconductance (2)	—	—	0.54*	D	$V_{GS} = 10V, I_D = 3.5A, T_C = 125^\circ\text{C}$
V_{SD} Diode Forward Voltage (2)	0.8*	—	1.8*	V	$T_C = 25^\circ\text{C}, I_S = 6.0A, V_{GG} = 0V$
g_{fs} Forward Transconductance (2)	1.5*	2.9	4.5*	S/(V)	$V_{DS} = 6V, I_D = 3.5A$
C_{iss} Input Capacitance	200*	450	600*	pF	$V_{GS} = 0V, V_{DS} = 26V, f = 1.0\text{ MHz}$
C_{oss} Output Capacitance	100*	200	400*	pF	See Fig. 10
C_{rss} Reverse Transfer Capacitance	20*	50	100*	pF	
t_{don} Turn-On Delay Time	—	—	40*	ns	$V_{DD} = 36V, I_D = 3.5A, Z_\theta = 500$
t_r Rise Time	—	—	70*	ns	See Fig. 15
t_{doff} Turn-Off Delay Time	—	—	40*	ns	MOSFET switching times are essentially independent of operating temperature.
t_f Fall Time	—	—	70*	ns	
SOA Safe Operating Area	20	—	—	W	$V_{GS} = 80V, I_D = 250\text{ mA}$, See Fig. 16.
	20	—	—	W	$V_{GS} = 3.3V, I_D = 60A$, See Fig. 16.

Thermal Resistance

$R_{\theta JC}$ Junction-to-Case	—	—	6.25*	$^\circ\text{C/W}$
$R_{\theta JA}$ Junction-to-Ambient	—	—	176	$^\circ\text{C/W}$ Free Air Operation

Source-Drain Diode Switching Characteristics (Typical)

t_{rr} Reverse Recovery Time	230	ns	$T_J = 160^\circ\text{C}, I_F = 6.0A, dI_F/dt = 100A/\mu\text{s}$
Q_{RR} Reverse Recovered Charge	1.2	μC	$T_J = 150^\circ\text{C}, I_F = 6.0A, dI_F/dt = 100A/\mu\text{s}$
t_{on} Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.		

① $T_J = 25^\circ\text{C}$ to 150°C . ② Pulse Test. Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

*JEDEC registered value

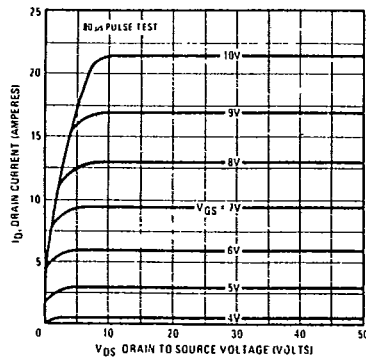


Fig. 1 - Typical Output Characteristics

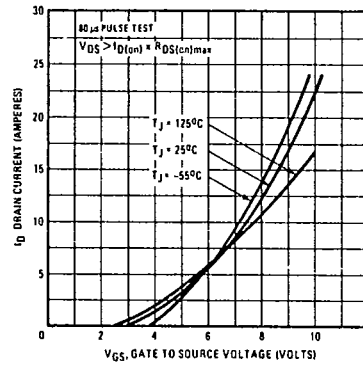


Fig. 2 - Typical Transfer Characteristics

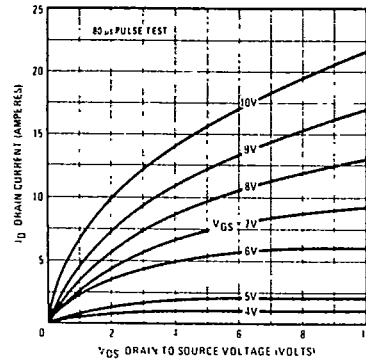


Fig. 3 - Typical Saturation Characteristics

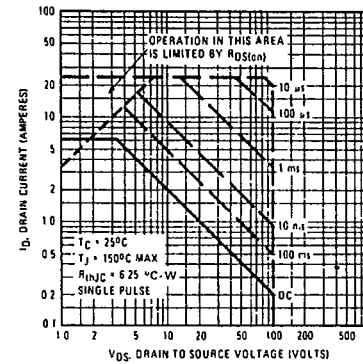


Fig. 4 - Maximum Safe Operating Area

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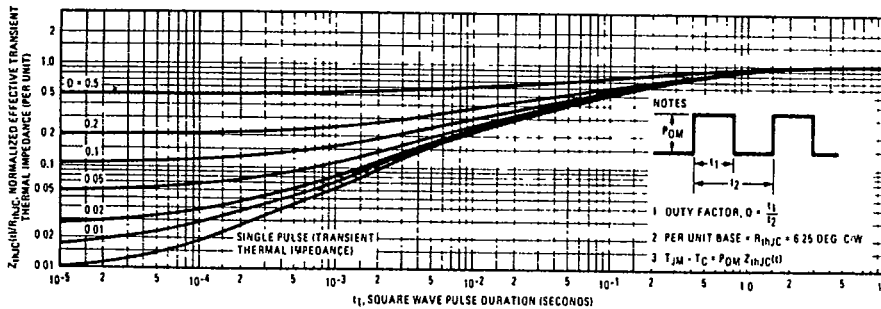


Fig. 5 - Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

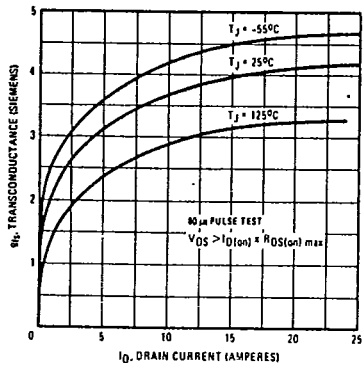


Fig. 6 - Typical Transconductance Vs. Drain Current

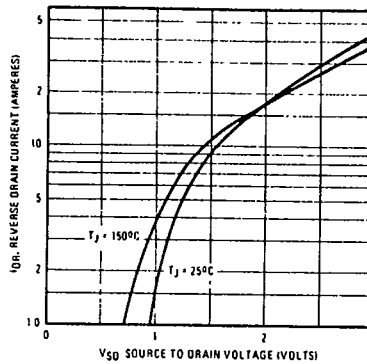


Fig. 7 - Typical Source-Drain Diode Forward Voltage

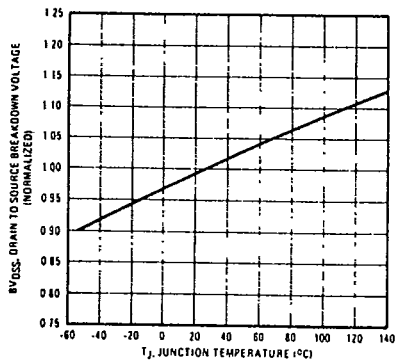


Fig. 8 - Breakdown Voltage Vs. Temperature

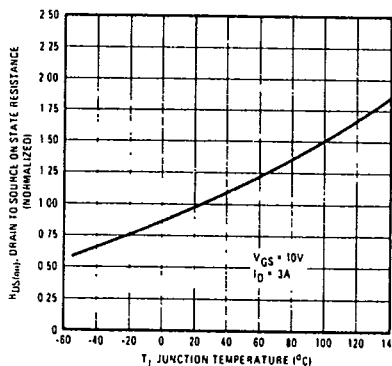


Fig. 9 - Normalized On-Resistance Vs. Temperature

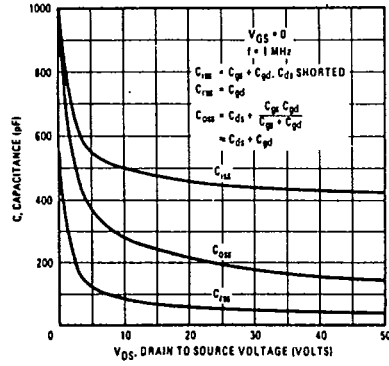


Fig. 10 - Typical Capacitance Vs. Drain-to-Source Voltage

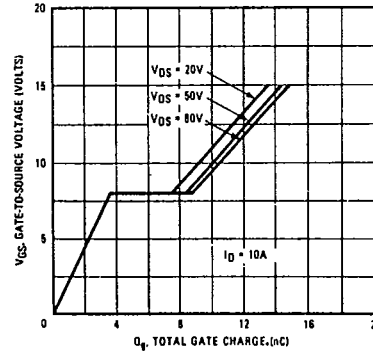


Fig. 11 - Typical Gate Charge Vs. Gate-to-Source Voltage

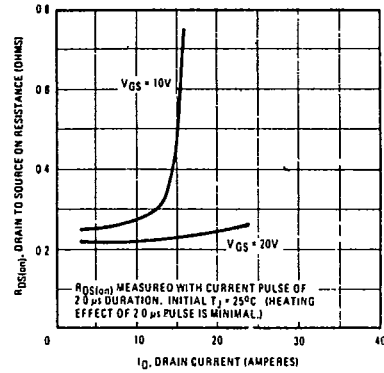


Fig. 12 - Typical On-Resistance Vs. Drain Current

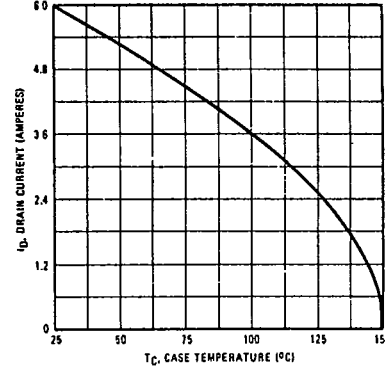


Fig. 13 - Maximum Drain Current Vs. Case Temperature

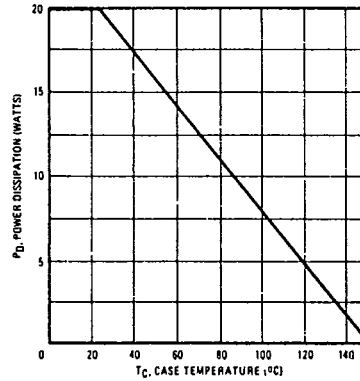
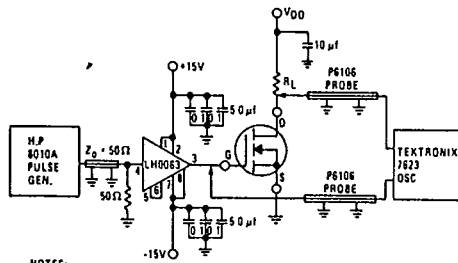
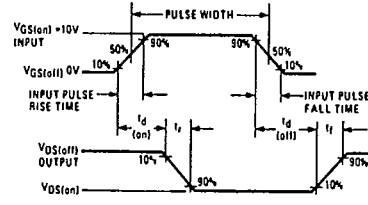


Fig. 14 - Power Vs. Temperature Derating Curve

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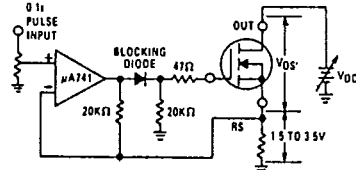


- NOTES:
1. LM0063 CASE GROUNDED
2. GROUNDED CONNECTIONS COMMON TO GROUND PLANE ON BOARD
3. PULSE WIDTH = 3 µs, PERIOD = 1 ms, AMPLITUDE = 10V.



NOTES
WHEN MEASURING RISE TIME, $V_{GS(on)}$ SHALL BE AS SPECIFIED ON THE INPUT WAVEFORM. WHEN MEASURING FALL TIME, $V_{GS(off)}$ SHALL BE SPECIFIED ON THE INPUT WAVEFORM. THE INPUT TRANSITION AND DRAIN VOLTAGE RESPONSE DETECTOR SHALL HAVE RISE AND FALL RESPONSE TIMES SUCH THAT DOUBLING THESE RESPONSES WILL NOT AFFECT THE RESULTS GREATER THAN THE PRECISION OF MEASUREMENT. THE CURRENT SHALL BE SUFFICIENTLY SMALL SO THAT DOUBLING IT DOES NOT AFFECT TESTS RESULTS GREATER THAN THE PRECISION OF MEASUREMENT.

Fig. 15 - Switching Time Test Circuit



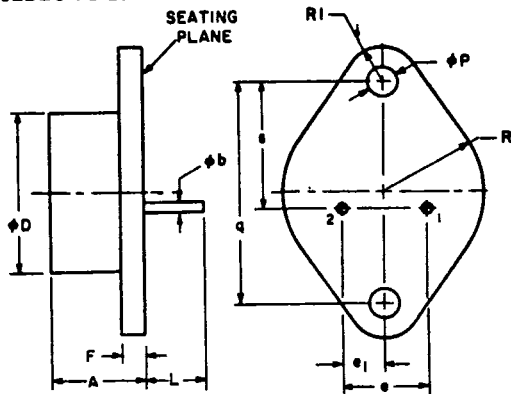
- NOTES
1. SET V_{DS} TO THE VALUE SPECIFIED UNDER DETAILS USING A 0.1µs PULSE WIDTH WITH A MINIMUM OF 1 MINUTE BETWEEN PULSES. INCREASE V_{DS} UNTIL THE SPECIFIED VALUE OF I_D AND V_{DS} ARE OBTAINED. CASE TEMPERATURE = 25°C
2. SELECT R_S SUCH THAT $I_D = R_S = 2.5 \pm 1.0$ Vdc

Fig. 16 - Safe Operating Area Test Circuit

Dimensional Outlines and Mounting Hardware

Dimensional Outlines

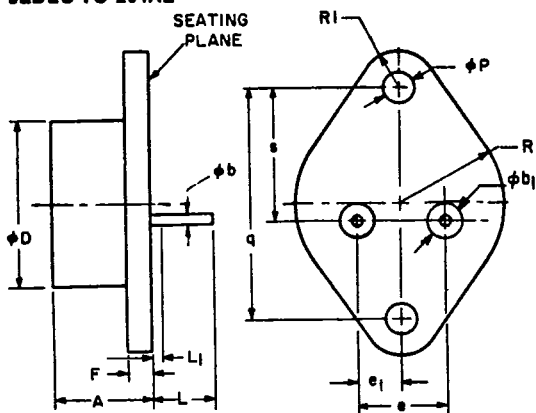
JEDEC TO-204AA



SYMBOL	INCHES		MILLIMETERS		NOTE
	MIN.	MAX.	MIN.	MAX.	
A	0.250	0.450	6.4	11.4	
phi b	0.038	0.043	0.968	1.092	
phi D	—	0.875	—	22.22	
e	0.420	0.440	10.67	11.17	
e1	0.205	0.225	5.21	5.71	
F	—	0.135	—	3.42	
L	0.312	—	7.93	—	
phi P	0.151	0.161	3.84	4.08	
q	1.187 BSC		30.15 BSC		
R	—	0.525	—	13.33	
R1	—	0.188	—	4.77	
s	0.655	0.675	16.64	17.14	

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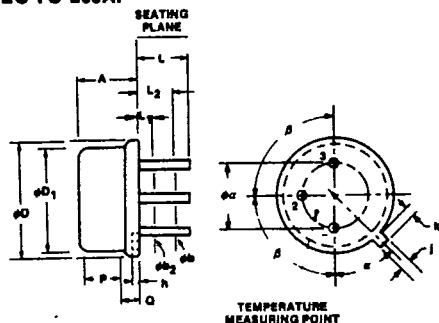
JEDEC TO-204AE



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	0.250	0.450	6.4	11.4	
phi b	0.057	0.063	1.45	1.60	
phi b1	0.141 NOM		3.58 NOM		
phi D2	—	0.875	—	22.22	
e	0.420	0.440	10.67	11.17	
e1	0.205	0.225	5.21	5.71	
F	0.060	0.135	1.53	3.42	
L	0.440	0.480	11.18	12.19	
phi P	0.151	0.161	3.84	4.08	
q	1.187 BSC		30.15 BSC		
R	0.495	0.525	12.58	13.33	
R1	0.131	0.168	3.33	4.77	
s	0.655	0.675	16.64	17.14	

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JEDEC TO-205AF



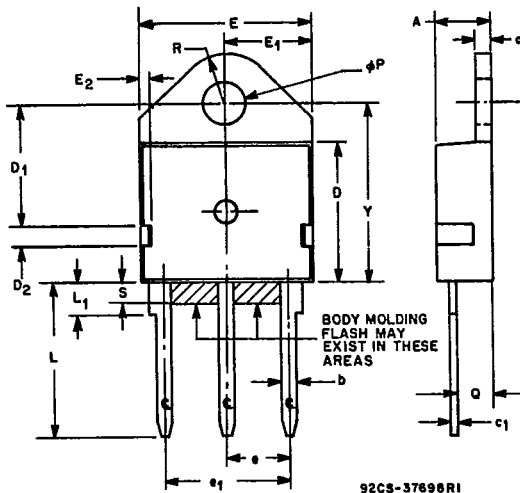
- Notes:
1. Dimension k measured from phi D maximum.
 2. phi D1 shall not vary more than 0.010 in Zone P. This zone controlled for automatic handling.
 3. Details of outline in this zone optional.
 4. Leads at gauge plane 0.054-0.055 below seating plane shall be within 0.007 radius of positional tolerance at MMC relative to tab at MMC. Device may be measured by direct methods or by gauge and gauging procedure described on JEDEC gauge drawing GS-1.
 5. phi b2 applies between L1 and L2. phi b applies between L2 and L minimum. Diameter is uncontrolled in L1 and beyond L minimum.

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
phi a	0.200 BSC		5.08 BSC		4
A	0.160	0.180	4.07	4.57	
phi b	0.016	0.021	0.41	0.53	5
phi b2	0.016	0.019	0.41	0.48	5
phi D	0.340	0.370	8.64	9.39	
phi D1	0.315	0.355	8.01	9.01	2
h	0.009	0.041	0.23	1.04	
j	0.028	0.034	0.72	0.86	
k	0.029	0.045	0.74	1.14	1
L	0.500	0.750	12.70	19.05	5
L1	—	0.050	—	1.27	5
L2	0.250	—	6.35	—	5
P	0.070	—	1.78	—	2
Q	—	0.050	—	1.27	3
alpha	45° NOMINAL				
beta	90° NOMINAL				

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Dimensional Outlines

JEDEC TO-218AC



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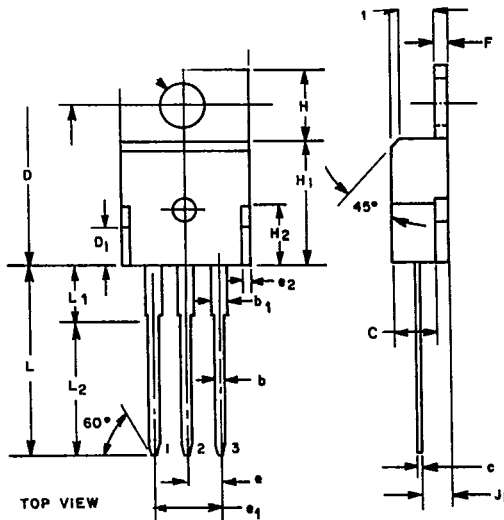
Notes:

- 1: Tab outline optional within boundaries of dimensions E and R.
- 2: Lead dimensions uncontrolled in L₁.
- 3: Controlling dimensions: Inch.

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	.165	.200	4.191	5.080	1
b	.040	.063	1.016	1.600	
c	.053	.065	1.346	1.651	
c ₁	.018	.030	.457	.762	
D	.485	.505	12.319	12.827	
D ₁	.395	.415	10.033	10.541	
D ₂	.070	.090	1.778	2.286	
E	.610	.640	15.494	16.256	
E ₁	.305	.320	7.747	8.128	
E ₂	.040	.060	1.016	1.524	
e	.205	.225	5.207	5.715	
e ₁	.420	.440	10.688	11.176	
L	.500	.610	12.700	15.494	
L ₁	—	.125	—	3.175	
phi P	.157	.167	3.988	4.241	
Q	.094	.126	2.388	3.200	
R	.170	.190	4.318	4.826	
S	—	0.60	—	1.524	
Y	.626	.670	15.900	17.018	

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JEDEC TO-220AB



92CS-34697R1

NOTES:

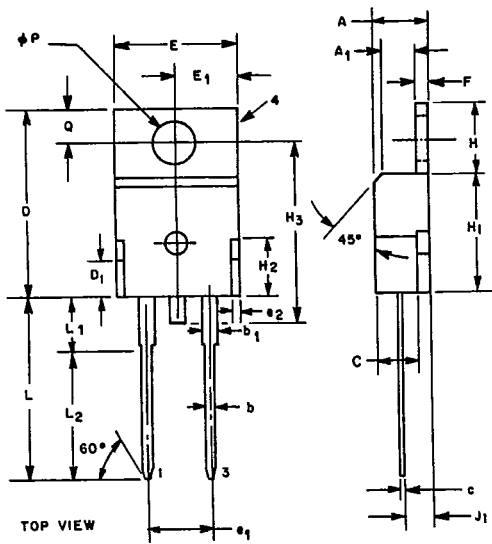
- 1. Position of lead to be measured 0.250-0.255 in. (6.350-6.477 mm) from case.

SYMBOL	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.140	0.190	3.56	4.82
A ₁	0.080	0.085	2.03	2.16
b	0.020	0.045	0.51	1.14
b ₁	0.045	0.070	1.14	1.77
C	—	0.125	—	3.18
c	0.015	0.025	0.38	0.63
D	0.560	0.625	14.23	15.87
D ₁	—	0.100	—	2.54
E	0.380	0.420	9.66	10.66
e	0.090	0.110	2.29	2.79
e ₁	0.190	0.210	4.83	5.33
e ₂	—	0.030	—	0.76
F	0.045	0.055	1.14	1.39
H	0.230	0.270	5.85	6.85
H ₁	0.355	0.370	9.02	9.40
H ₂	—	0.160	—	4.06
J ₁	0.080	0.115	2.04	2.92
L	0.500	0.562	12.70	14.27
L ₁	—	0.250	—	6.35
L ₂	0.400	0.410	10.16	10.41
phi P	0.139	0.161	3.531	4.089
Q	0.100	0.120	2.54	3.04

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Dimensional Outlines

JEDEC TO-220AC



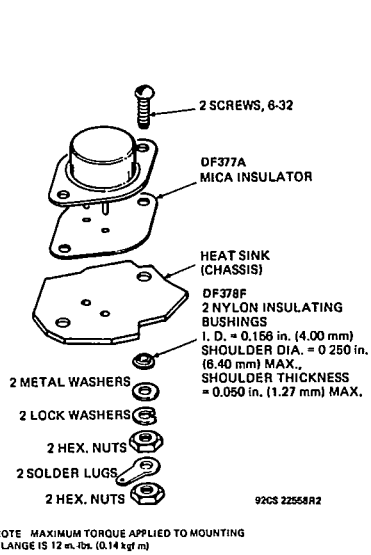
NOTES:

1. Position of lead to be measured 0.250-0.255 in. (6.350-6.477 mm) from case.

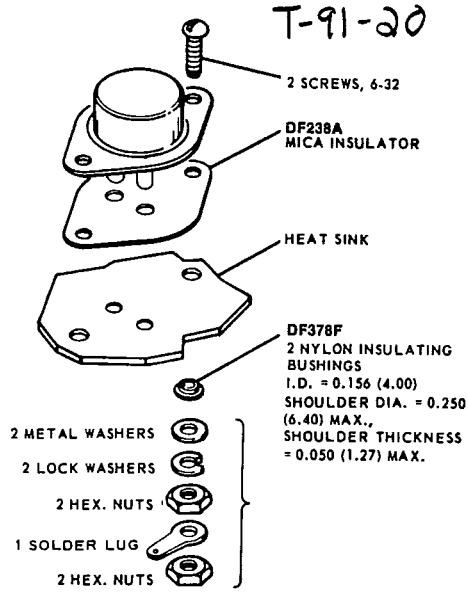
SYMBOL	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.140	0.190	3.56	4.82
A ₁	0.080	0.085	2.03	2.16
b	0.020	0.045	0.51	1.14
b ₁	0.045	0.070	1.14	1.77
C	—	0.125	—	3.18
c	0.015	0.025	0.38	0.63
D	0.560	0.825	14.23	15.87
D ₁	—	0.100	—	2.54
E	0.380	0.420	9.66	10.66
e ₁	0.190	0.210	4.83	5.33
e ₂	—	0.030	—	0.76
F	0.045	0.055	1.14	1.39
H	0.230	0.270	5.85	6.85
H ₁	0.355	0.370	9.02	9.40
H ₂	—	0.160	—	4.06
H ₃	—	0.600	—	15.24
J ₁	0.080	0.115	2.04	2.92
L	0.500	0.562	12.70	14.27
L ₁	—	0.250	—	6.35
L ₂	0.400	0.410	10.16	10.41
ϕP	0.139	0.161	3.531	4.089
Q	0.100	0.120	2.54	3.04

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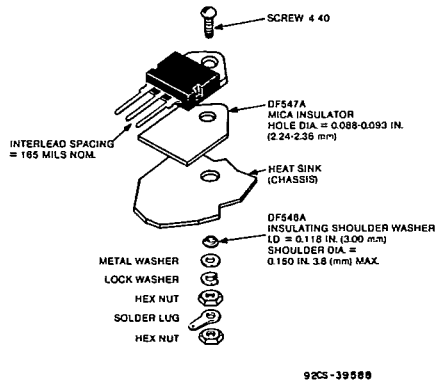
Mounting Hardware



Suggested mounting hardware for JEDEC TO-204AA
(formerly JEDEC TO-3)



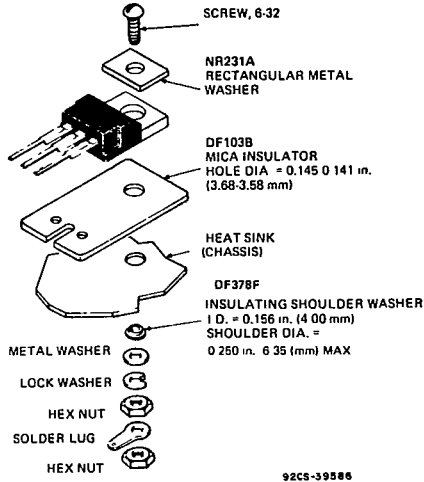
Suggested mounting hardware for JEDEC TO-204AE
(formerly JEDEC TO-3)



Suggested mounting hardware for JEDEC TO-218AC

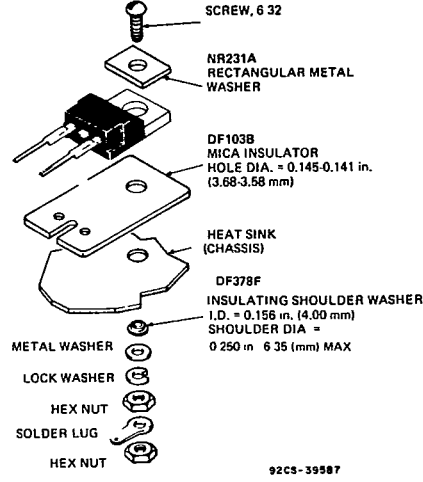
T-91-20

Mounting Hardware



NOTE: MAXIMUM TORQUE APPLIED TO MOUNTING FLANGE IS 8 in. lb. (0.09 kgf m)

Suggested mounting hardware for JEDEC TO-220AB



NOTE: MAXIMUM TORQUE APPLIED TO MOUNTING FLANGE IS 8 in. lb. (0.09 kgf m)

Suggested mounting hardware for JEDEC TO-220AC